BJT (Bipolar junction Transistor)

Active mode VBE = 0.7V

Le= xiE

LE = ibtic

ic = Bib

Saturation mode

VBE = 0.8 V

VCE = 0.2 V

ie = 16+ ic

check ic < BiB

· Cut-off

VBE < 0.5 V

VCE - VCC

10 = 0

18 = 0

IE = O

check VCE 70.2V

VBC <0.5V

B= 0

JFET (Junction Field Effect Transistor) or depletion MOSFET

if Vois < Vp : Cutoff made

if VGs > VP and VDS < VGS - VP : Ohmic mode

 $I_D = I_{DSS} \left[2 \left(1 - \frac{V_{GS}}{V_p} \right) \left(\frac{V_{DS}}{-V_p} \right) - \left(\frac{V_{DS}}{V_p} \right)^2 \right]$

if VGS > VP and VDS > VGS - Vp: active / saturation mode

ID = IDSS (1- VGS)

Vn Frm Fic= 9mVn

 $9m = \frac{Ic}{VT}$ $r_{\pi} = \frac{B}{9m}$

Small signal analysis

HML = VIL - VOL

NMH = YOH - VIH

enhancement mosfet

VGS < VT : Lutoff mode

if VDS € VGS-VT: Ohmic mode

ID = K[2(VGS-V+)VDS-(VDS)]

if VDS > VGS-VT: active | Saturation mode

ID = K (VGS-VT)2

BiB > i'n + 'B current to Vout townent going out Diode

Semi conductors

$$p = \frac{ni^2}{ND} \qquad n = \frac{ni^2}{NA}$$

x < wo undamped

a = wo critically damped

x y wo owidamped

in
$$dB = 10 \log \left(\frac{P_z}{P_z}\right) = 20 \log \left(\frac{V_z}{V_z}\right) = 20 \log |H|$$

Pour gain =
$$\frac{P_2}{P_1}$$

